

**C630-55V**

Red LED CHIP

<Specifications>

Commodity Type and Physical Characteristics	
Material	InGaAlP/GaAs
Top Side P(anode)side	Au Alloy/Al or Au Pad
Bottom Side N(cathode)side	Au Alloy
Electrode Pattern	Fig.1
Chip Size	Fig.2
Chip Thickness	Fig.2
Emission Area	Fig.2

Electro-Optical Characteristics [Ta=25°C]						
Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	IF=20mA		1.8	2.1	V
	Vfp	I <sub>fp</sub> =500mA		3.00	4.50	
Reverse Current	IR	VR=5V			10	uA
Brightness	IV	IF=20mA	70	120		mcd
Power Intensity	PO	IF=20mA	0.7	1.2		mW
Peak Wavelength	λP	IF=20mA	625	635	645	nm
Spectral Radiation Bandwidth	Δλ	IF=20mA		15		nm
Rise Time	tr	IF=20mA		100		ns
Fall Time	tf	IF=20mA		100		ns

Pulse Forward Current condition: Duty=1% and Pulse Width = 1μs  
 Die shall be mounted on TO-18 gold header without resin coated.

[Unit:um]

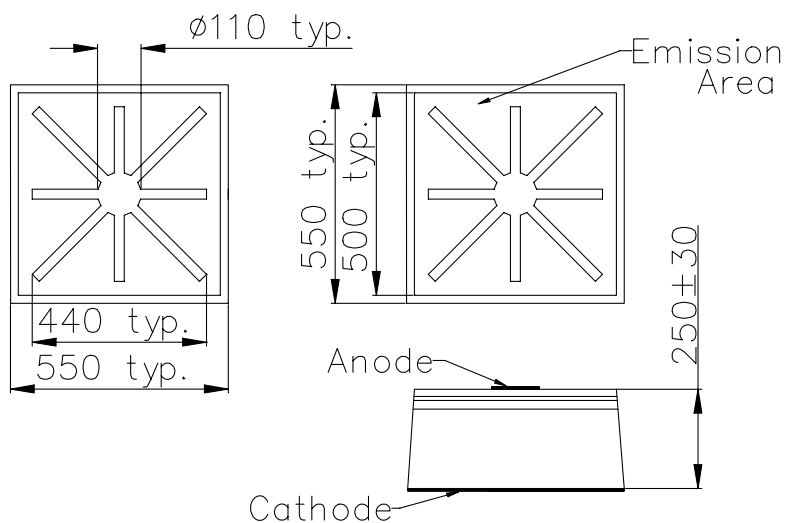


Fig.1 Electrode Pattern

Fig.2 Chip Size and Emission Area